

<Hybrid-SiC Modules>

CMH600DU-24NFH

HIGH POWER SWITCHING USE
INSULATED TYPE



dual switch (Half-Bridge)

Collector current I_C 600 A
Collector-emitter voltage V_{CES} 1200 V
Maximum junction temperature T_{jmax} 150 °C

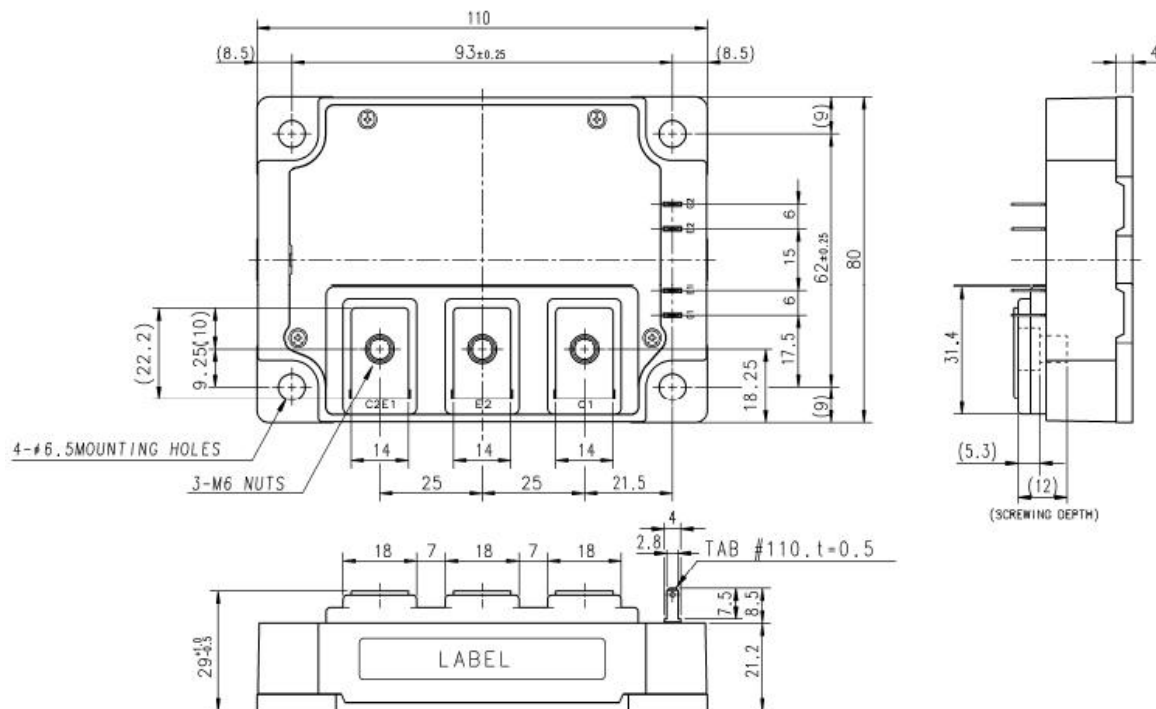
- Silicon IGBT + Silicon Carbide Schottky Barrier Diode
- Flat base Type
- Copper base plate
- RoHS Directive compliant
- Recognized under UL1557, File E323585

APPLICATION

High frequency switching use(30kHz to 60kHz)
Gradient magnetic power supply, Induction heating, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

Dimension in mm



INTERNAL CONNECTION

Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

CMH600DU-24NFHHIGH POWER SWITCHING USE
INSULATED TYPEMAXIMUM RATINGS ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise specified, per 1/2 module)

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=25\text{ }^{\circ}\text{C}$ (Note2, 4)	600	A
I_{CRM}		Pulse, Repetitive (Note3)	1200	
P_{tot}	Total power dissipation	$T_C=25\text{ }^{\circ}\text{C}$ (Note2, 4)	3670	W
I_E (Note1)	Emitter current	DC, $T_C=25\text{ }^{\circ}\text{C}$ (Note2, 4)	600	A
I_{ERM} (Note1)		Pulse, Repetitive (Note3)	1200	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, f=60 Hz, AC 1 min	4000	V
T_j	Junction temperature	- (Note8)	$-40 \sim +150$	$^{\circ}\text{C}$
T_{stg}	Storage temperature	-	$-40 \sim +125$	

ELECTRICAL CHARACTERISTICS ($T_J=25\text{ }^{\circ}\text{C}$, unless otherwise specified, per 1/2 module)

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$, G-E short-circuited	-	-	30.0	mA
I_{GES}	Gate-emitter leakage current	$V_{GE}=V_{GES}$, C-E short-circuited	-	-	2.0	μA
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=60\text{ mA}$, $V_{CE}=10\text{ V}$	4.5	6.0	7.5	V
V_{CESat}	Collector-emitter saturation voltage	$I_C=600\text{ A}$, $V_{GE}=15\text{ V}$ (Note5)	$T_J=25\text{ }^{\circ}\text{C}$	-	5.0	V
		Refer to the figure of test circuit	$T_J=125\text{ }^{\circ}\text{C}$	-	5.0	
C_{ies}	Input capacitance	$V_{CE}=10\text{ V}$, G-E short-circuited	-	-	95	nF
C_{oes}	Output capacitance		-	-	8.0	
C_{res}	Reverse transfer capacitance		-	-	1.8	
Q_G	Gate charge	$V_{CC}=600\text{ V}$, $I_C=600\text{ A}$, $V_{GE}=15\text{ V}$	-	2700	-	nC
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600\text{ V}$, $I_C=600\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.52\text{ }\Omega$, Inductive load	-	-	400	ns
t_r	Rise time		-	-	120	
$t_{d(off)}$	Turn-off delay time		-	-	700	
t_f	Fall time		-	-	150	
V_{EC} (Note1)	Emitter-collector voltage	$I_E=600\text{ A}$, G-E short-circuited (Note5)	$T_J=25\text{ }^{\circ}\text{C}$	-	1.7	V
		Refer to the figure of test circuit	$T_J=125\text{ }^{\circ}\text{C}$	-	2.2	
Q_C (Note1)	Collector - emitter charge	$V_{CC}=600\text{ V}$, $I_E=600\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.52\text{ }\Omega$, Inductive load	-	4.0	-	μC
E_{on}	Turn-on switching energy per pulse	$V_{CC}=600\text{ V}$, $I_C/I_E=600\text{ A}$,	-	10.0	-	mJ
E_{off}	Turn-off switching energy per pulse	$V_{GE}=\pm 15\text{ V}$, $R_G=0.52\text{ }\Omega$,	-	26.0	-	
E_{rec} (Note1)	Reverse energy per pulse	$T_J=125\text{ }^{\circ}\text{C}$, Inductive load	-	1.9	-	mJ
r_g	Internal gate resistance	Per switch	-	0.53	-	Ω

THERMAL RESISTANCE CHARACTERISTICS (per 1/2 module)

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
$R_{th(j-c)Q}$	Thermal resistance	Junction to case (Note4)	-	-	0.034	K/W
$R_{th(j-c)D}$		Junction to case (Note4)	-	-	0.082	
$R_{th(c-s)}$	Contact thermal resistance	Case to heat sink, Thermal grease applied (Note4, 6, 8)	-	0.02	-	K/W

Caution; No short-circuit capability is designed.

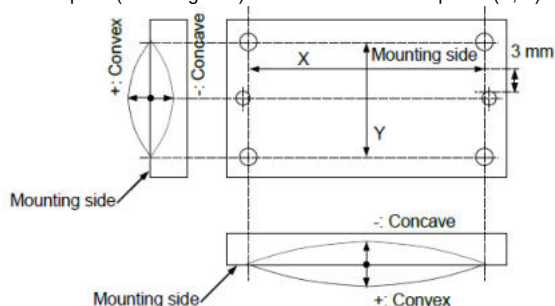
CMH600DU-24NFHHIGH POWER SWITCHING USE
INSULATED TYPE**MECHANICAL CHARACTERISTICS**

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M_t	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
M_s	Mounting torque	Mounting to heat sink M 6 screw	3.5	4.0	4.5	N·m
d_s	Creepage distance	Terminal to terminal	17.0	-	-	mm
		Terminal to base plate	32.0	-	-	
d_a	Clearance	Terminal to terminal	11.0	-	-	mm
		Terminal to base plate	28.1	-	-	
m	mass	-	-	580	-	g
e_c	Flatness of base plate	On the centerline X (Note7)	-100	-	100	μm
		On the centerline Y (Note7)	-100	-	100	

*: This product is compliant with the Restriction of the Use of Certain Hazardous Substances in Electrical and Electronic Equipment (RoHS) directive 2011/65/EU and (EU) 2015/863.

Note1. Represent ratings and characteristics of the anti-parallel, emitter-collector free-wheeling diode (DIODE).

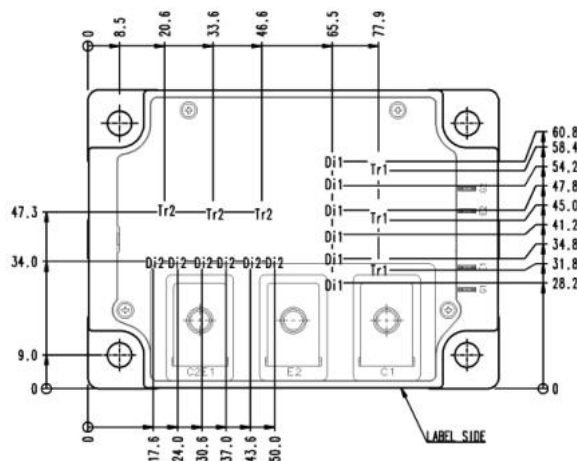
- Junction temperature (T_j) should not increase beyond $T_{j\text{max}}$ rating.
- Pulse width and repetition rate should be such that the device junction temperature (T_j) does not exceed $T_{j\text{max}}$ rating.
- Case temperature (T_c) and heat sink temperature (T_s) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
- Pulse width and repetition rate should be such as to cause negligible temperature rise.
- Typical value is measured by using thermally conductive grease of $\lambda=0.9 \text{ W/(m}\cdot\text{K)}$.
- The base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



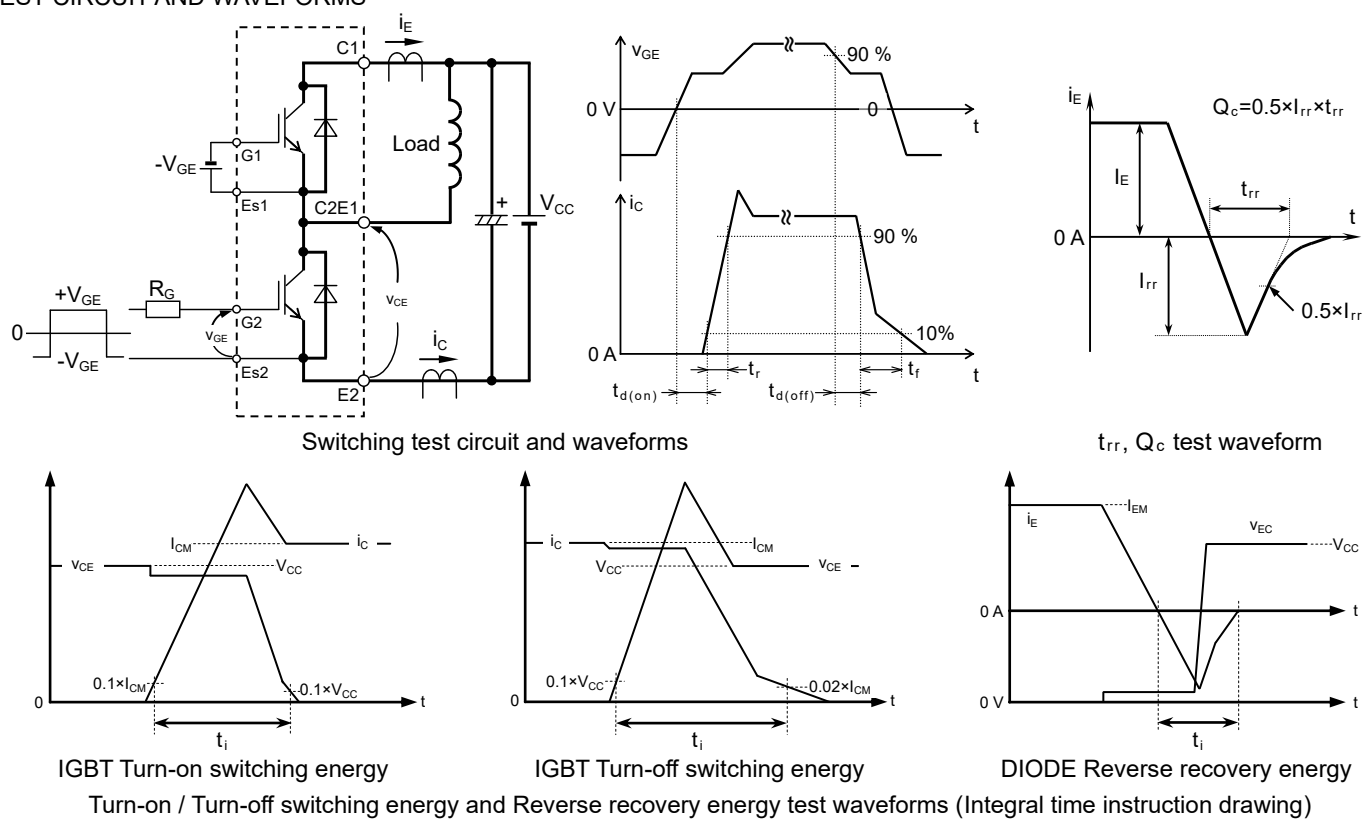
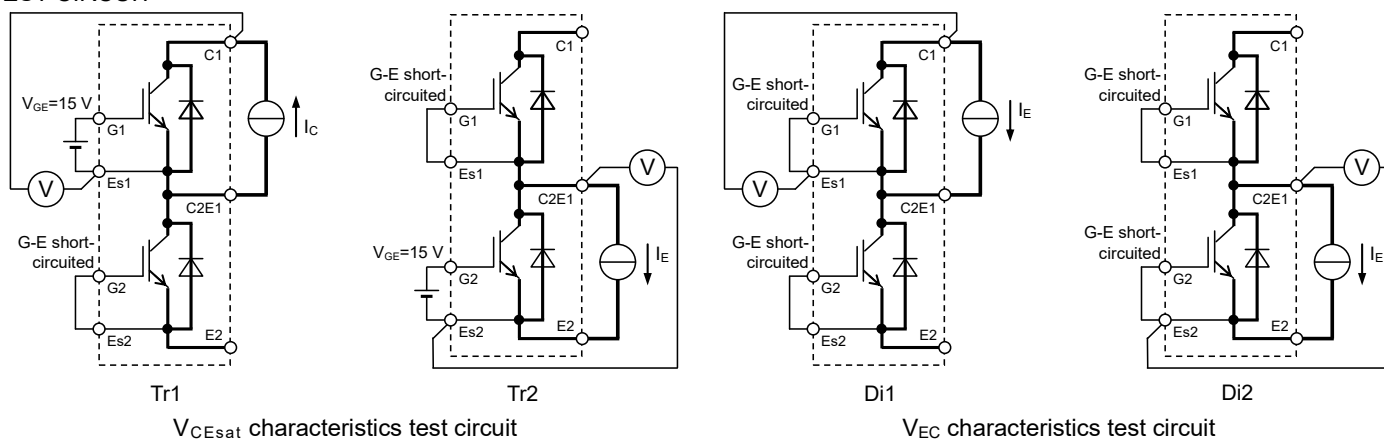
- Long term performance related to thermal conductive material such as thermal grease (including but not limited to aspects such as the increase of thermal resistance due to pumping out, etc.) should be verified under your specific application conditions. Temperature condition (T_j) must be maintained below the maximum rated temperature throughout consideration of the temperature rise even for long term usage.

RECOMMENDED OPERATING CONDITIONS

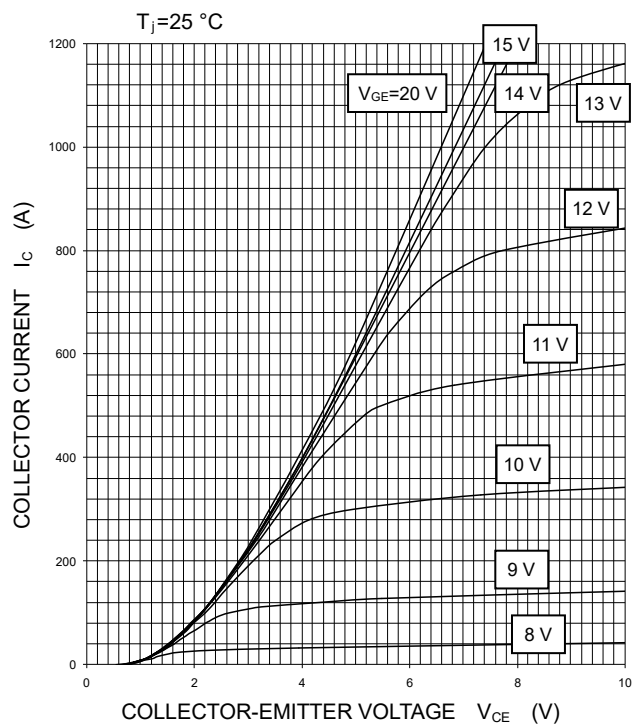
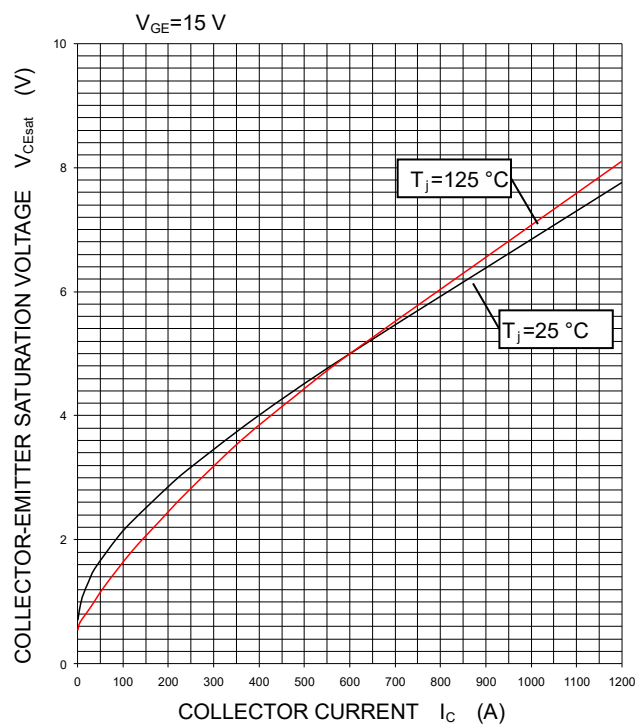
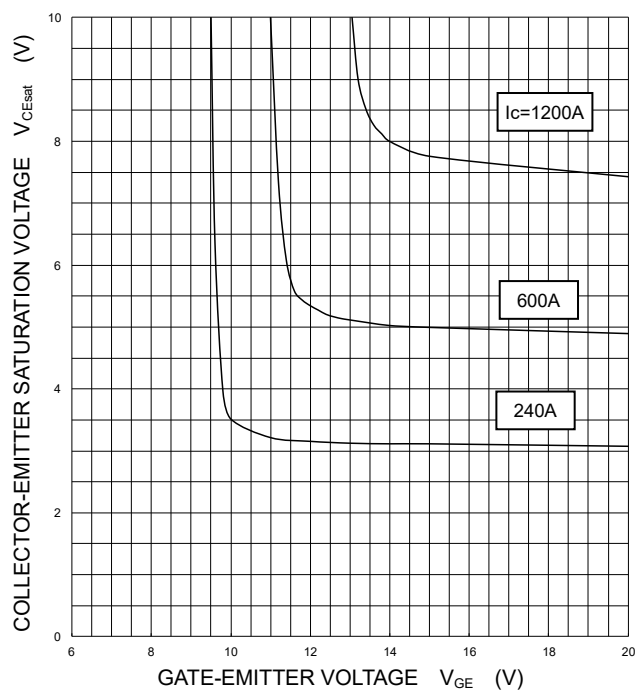
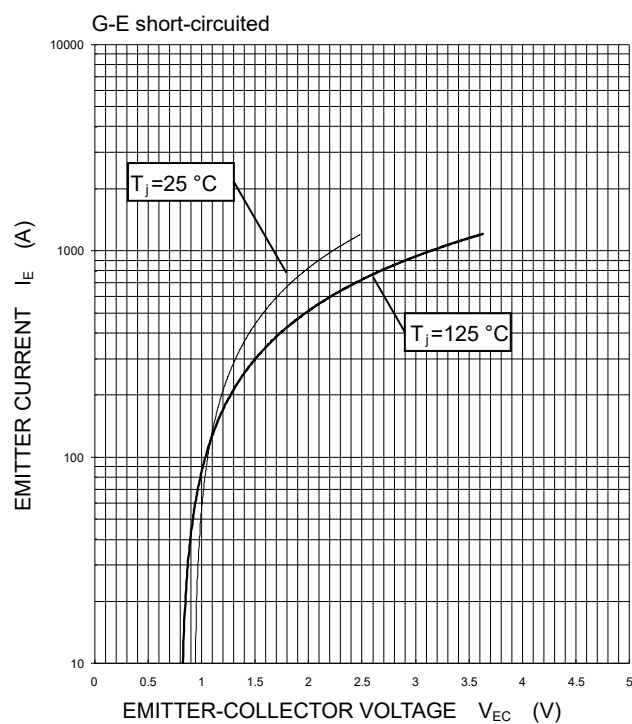
Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across C1-E2 terminals	-	600	800	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2 terminals	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	0.52	-	5.2	Ω

CHIP LOCATION (Top view)Dimension in mm, tolerance: $\pm 1 \text{ mm}$ 

Tr1/Tr2: IGBT, Di1/Di2: DIODE

CMH600DU-24NFHHIGH POWER SWITCHING USE
INSULATED TYPE**TEST CIRCUIT AND WAVEFORMS****TEST CIRCUIT**

PERFORMANCE CURVES

OUTPUT
CHARACTERISTICS
(TYPICAL)COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)COLLECTOR-EMITTER SATURATION VOLTAGE
CHARACTERISTICS
(TYPICAL)FREE WHEELING DIODE
FORWARD CHARACTERISTICS
(TYPICAL)

CMH600DU-24NFH

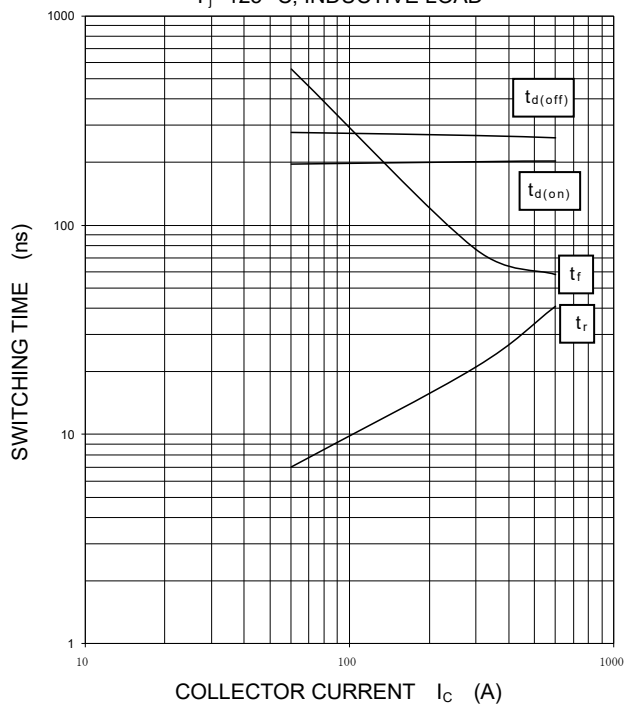
HIGH POWER SWITCHING USE

INSULATED TYPE

PERFORMANCE CURVES

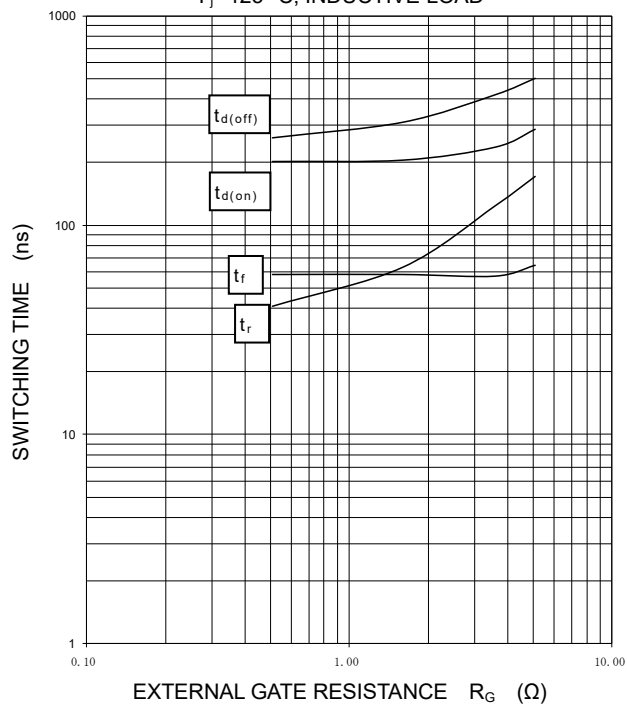
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.52\ \Omega$,
 $T_J=125\text{ }^\circ\text{C}$, INDUCTIVE LOAD



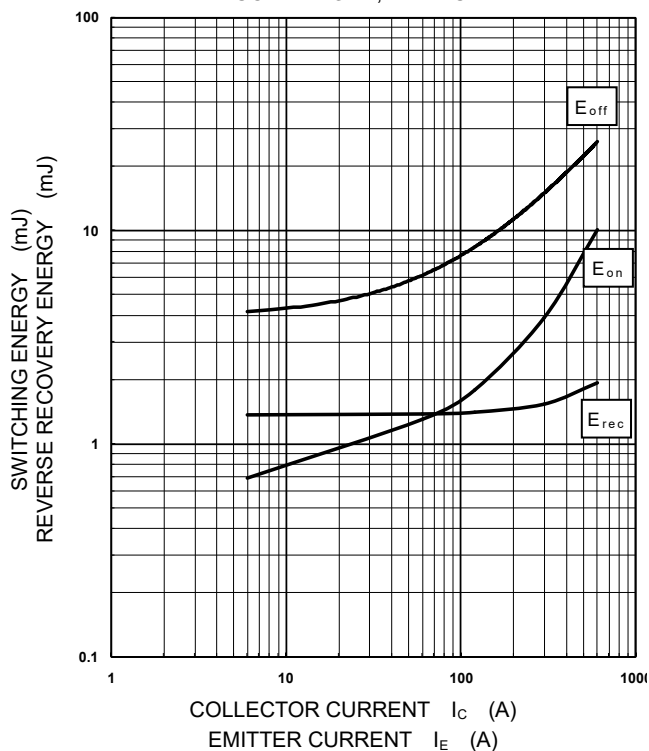
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C=600\text{ A}$,
 $T_J=125\text{ }^\circ\text{C}$, INDUCTIVE LOAD



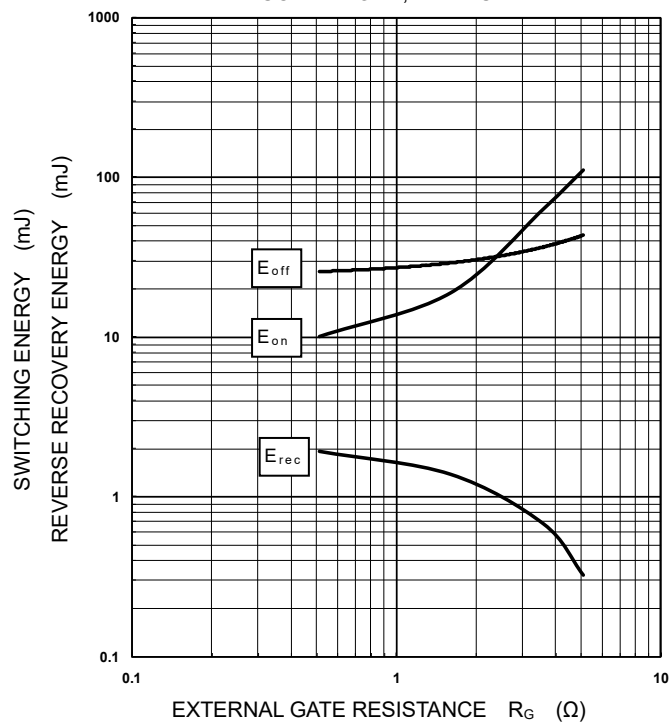
HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=0.52\ \Omega$, $T_J=125\text{ }^\circ\text{C}$,
INDUCTIVE LOAD, PER PULSE

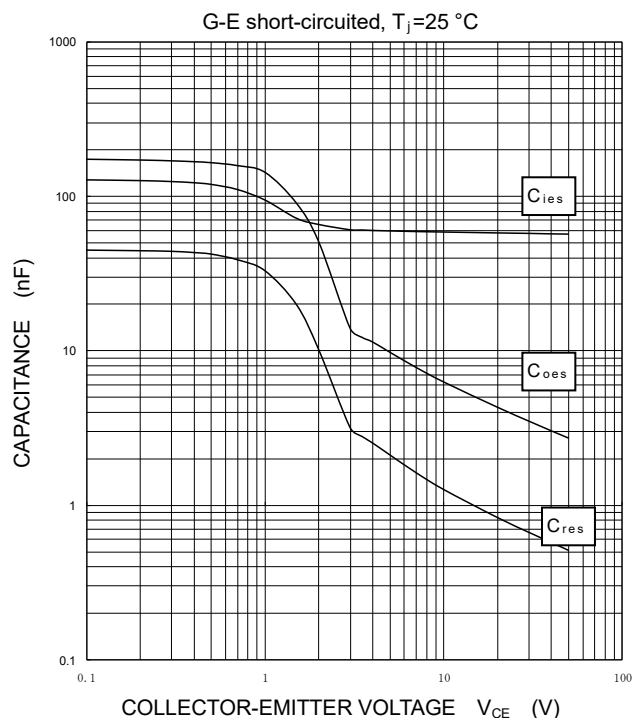
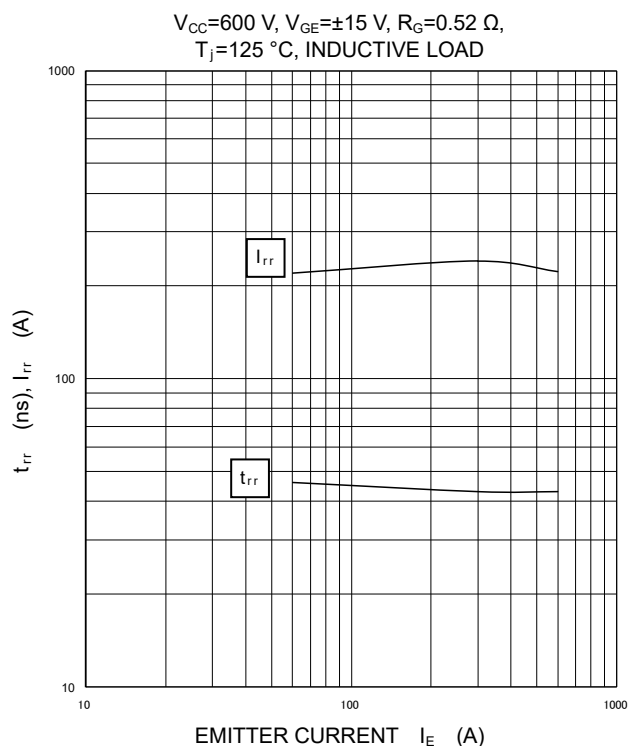
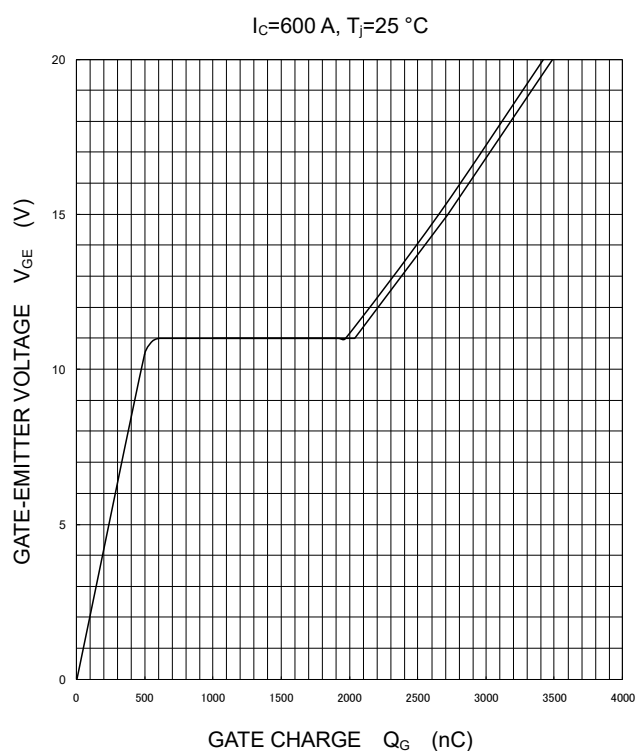
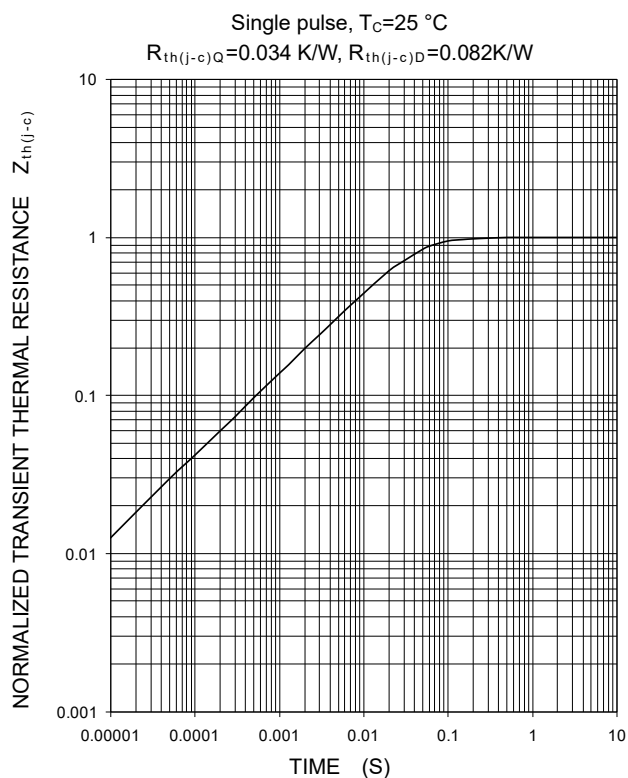


HALF-BRIDGE
SWITCHING CHARACTERISTICS
(TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $I_C/I_E=600\text{ A}$, $T_J=125\text{ }^\circ\text{C}$,
INDUCTIVE LOAD, PER PULSE



PERFORMANCE CURVES

CAPACITANCE
CHARACTERISTICS
(TYPICAL)FREE WHEELING DIODE
REVERSE RECOVERY CHARACTERISTICS
(TYPICAL)GATE CHARGE
CHARACTERISTICS
(TYPICAL)TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS
(MAXIMUM)

Note: The characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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CMH600DU-24NFHHIGH POWER SWITCHING USE
INSULATED TYPE**Keep safety first in your circuit designs!**

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